

EAST - [10809651.wsp.1]

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- L1: (3039) intermetal adj dielectric adj layer or IDL
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DBs: USPAT, US-PGPUB, EPO, JPO

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1 and DRAM

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2	R	I	US 20040102001 A1	20040527	6	Three layer aluminum deposition process for high aspect ratio CL contacts	438/239	438/256; 438/688
3	R	I	US 20040099965 A1	20040527	26	Integrated circuits having self-aligned metal contact structures	1/1	
4	R	I	US 20040098208 A1	20040520	24	Methods, systems and computer programs for deconvolving the spectral	702/32	
5	R	I	US 20040094778 A1	20040520	73	Semiconductor device and semiconductor memory device provided with internal	257/202	
6	R	I	US 20040087098 A1	20040506	14	MIM AND METAL RESISTOR FORMATION AT CU BEOL USING ONLY ONE EXTRA	438/381	
7	R	I	US 20040073105 A1	20040415	15	Cardiac diagnostics using wall motion and perfusion cardiac MRI imaging and	600/410	
8	R	I	US 20040072439 A1	20040415	16	Chemical mechanical polishing composition and process	438/694	
9	R	I	US 20040042387 A1	20040304	178	Communication system with multicarrier telephony transport	370/206	
10	R	I	US 20040042292 A1	20040304	26	Semiconductor device	365/202	
11	R	I	US 20040041263 A1	20040304	31	Integrated circuit with modified metal features and method of fabrication	257/752	
12	R	I	US 20040029374 A1	20040212	6	Compact semiconductor structure and method for producing the same	438/618	438/624; 438/637;